の) 4=0 for 1×12号 b) first : kinetic energy second: potential energy 2 c) Y(x) = Aejkx + Bejkx or A sinckx) + B cosckx) d) 4(-=)=0, 4(=)=0 e) CAsin(k. +) + BCos(k. +)=0 0 Asin(-k. =) + Boos(-k. =)=0 => - Asin(k. =) + Boos(k. =)=0 @ () + () . () - () => (sin(k. \(\frac{1}{2} \)) = 0 or \(\begin{picture}(\frac{1}{2} \) = 0 or \(\beta = 0 \)
\(\cos(k. \frac{1}{2} \)) = 0 or \(\beta = 0 \) ς if sinck+=)=0, B=0 ⇒k== nT ⇒k===== +(x)=ASin(===x) n=1,2.3... if cos(k. =)=0, A=0 => k. == cn+=)T => k= (2n+1)T => Y(x)=Pcos((2n+1)T x) n=0.1.2.3... $E = Ep + Ek = Ek = \frac{p^{2}}{2m} = \left(\frac{2 + \sqrt{n}}{m}\right)^{2} = \left(\frac{2 + \sqrt{$ Normalize: 50 4"(x) 4(x) = 0 => 5 = 4(x) dx = 0 => A=B= == So $\psi(x) = \begin{cases} \int_{-L}^{2} \sin(\frac{2\pi T}{L}x) & n = 1.2.3... \\ E_{L} = \frac{2\pi^{2} T^{2}}{mL^{2}} & \text{for } -\frac{L}{2} \leq x \leq \frac{L}{2} \end{cases}$ $\int_{-L}^{2} \cos(\frac{(2\pi T)T}{L}x) & n = 0.1.2.3... \\ E_{L} = \frac{\pi^{2}(2\pi T)^{2}T^{2}}{2mL^{2}} & \text{for } -\frac{L}{2} \leq x \leq \frac{L}{2}$ f > first: ψ(x) = \(\frac{2}{L} \cos \frac{πx}{L} \) Second: $\psi(x) = \sqrt{\frac{1}{L}} \sin \frac{2\pi i x}{L}$ third: $\psi(x) = \int_{-\frac{\pi}{2}}^{2} \cos \frac{3\pi x}{L}$ (this is also correct if you flip the sign of $\psi(x)$)

even you multiply it by |u| = 1, α is a complex number)



A more clever approach is to switch the roordnote from 0+1 to $-\frac{1}{2} \rightarrow \frac{1}{2}$, the case of 0-1 is discussed in the class!

in this case $Y(x) = \sqrt{\frac{1}{2}} \sin \left(\frac{n^{\frac{1}{2}}}{n^{\frac{1}{2}}} (x + \frac{1}{2}) \right) = 1.2.3...$ $E = \frac{n^{\frac{1}{2}} \pi^{\frac{1}{2}}}{2n L^{\frac{1}{2}}}$

2)

(A)
$$I = \frac{1}{2m} \frac{\partial^2 V(x)}{\partial x^2} + V_0 V(x) = E V(x) = 7 V_0(x) = A_1 e^{k_1 x}$$
 $V = \infty$
 $V = \infty$

c)
$$\beta_2 = A_1 = \frac{k_2}{k_1} A_2$$
 from Q and Q

From (3):
$$\frac{k_2 \sin (k_2 \alpha)}{k_1} + \frac{k_2}{k_1} \frac{k_2}{k_2} \cos (k_2 \alpha) = 0$$
 Az cont be 0
 $\sin (\sqrt{\frac{\log \alpha}{h^2}} \alpha) + \sqrt{\frac{E}{V^0 - E}} \cos (\sqrt{\frac{\log \alpha}{h^2}} \alpha) = 0$

7)

e)
$$E_{k} = \frac{p^{2}}{2m^{5}} = \frac{\pi t^{2}}{32 a^{2} \cdot 0.4 eV}$$
 $mp^{*} = \frac{\pi t^{2}}{32 a^{2} \cdot 0.4 eV}$
 $3' \quad \text{or} \quad \zeta.35 \times 10^{-5} \frac{1}{a^{2}}$

$$V = \frac{P}{mp^*} = -\frac{8a \cdot 0.41ev}{11h} 3' \text{ or } -1.55 \times 10^{15} a$$

3: photon-electric effect, double-slit interference for single electron or photon, hydrogen spectrum, stability of atom, Compton scattering, randomness of radioactivity... List whatever you find on the Internet will be OK.

5: band gap: Insulator>semiconductor>metal

At 0K: No electron can receive thermal energy to be excited from the valence band to the conduction band in semiconductor. In metal, electrons don't need to be excited to participate in the conduction process.

6: Doping is we add impurities intentionally to semiconductor like silicon. It enables us to control semiconductors' properties like conductivity so that we can engineer these materials based on our need. P-type dopants tend to attract electrons from semiconductor while N-type dopants tend to give electrons. P-type: B, Al, Ga···. N-type: N, P, As···.